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## PATENT ABSTRACTS OF JAPAN

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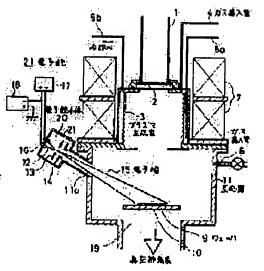
(72)Inventor: ISHIOKA HISAMICHI

## (54) FORMATION OF THIN FILM

### (57)Abstract:

PURPOSE: To obtain a dense insulating film having a low hydrogen concn. and satisfactory molecular bond on the surface of a wafer without heating the wafer by irradiating the surface of the wafer with electron beams during or after the formation of a thin film on the surface of the wafer by plasma CVD.

CONSTITUTION: An electron gun 21 for emitting electron beams is fitted to an ECR plasma CVD device so that the body 20 of the electron gun 21 is fixed in an opening 11a pierced in the side wall of a reaction chamber 11. When a thin film is formed on the surface of a wafer 9, the surface of the wafer 9 is irradiated with electron beams 15 from the electron gun 21 during or after the formation of the thin film so that electrons are showered on the entire surface of the wafer 9. Since the wafer is not heated, the thin film can be formed at a low temp. without heating an Al circuit having low heat resistance to a high temp.



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